Characteristics (T_j = 25°C) **Kennwerte (T_j = 25°C)**

		Min.	Typ.	Max.
Collector-Base cutoff current – Kollektor-Basis-Reststrom				
V_{CB} = 25 V, (E open)	I_{CBO}	–	–	100 nA
Emitter-Base cutoff current – Emitter-Basis-Reststrom				
V_{EB} = 4 V, (C open)	I_{EBO}	–	–	100 nA
Transition Frequency – Transitfrequenz				
V_{CE} = 5 V, I_C = 50 mA, f = 100 MHz	f_T	–	170 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität				
V_{CB} = 10 V, $I_E = i_e$ = 0, f = 1 MHz	C_{CBO}	–	3 pF	–
Thermal resistance junction to soldering point Wärmewiderstand Sperrschicht – Lötpunkt	R_{thsp}	< 70 K/W		
Recommended complementary PNP transistors Empfohlene komplementäre PNP-Transistoren		BC807K / BC808K		
Marking of available current gain groups per type Stempelung der lieferbaren Stromverstärkungsgruppen pro Typ	BC817K-16 = 6A or 6CR BC817K-25 = 6B or 6CS BC817K-40 = 6C or 6CT	BC818K-16 = 6E or 6CR BC818K-25 = 6F or 6CS BC818K-40 = 6G or 6CT		